



PATENT
3672-0110P

IN THE U.S. PATENT AND TRADEMARK OFFICE

Applicant: ROMAN et al. Conf.:
Appl. No.: 09/720,329 Group: 2818
Filed: February 6, 2001 Examiner: D. Vu
For: A METHOD IN FABRICATION OF ORGANIC
THIN-FILM SEMICONDUCTING DEVICES

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TECHNOLOGY CENTER 3300

LARGE ENTITY TRANSMITTAL FORM

Assistant Commissioner for Patents
Washington, DC 20231

September 7, 2001

Sir:

Transmitted herewith is an amendment in the above-identified application.

- ☐ The enclosed document is being transmitted via the Certificate of Mailing provisions of 37 C.F.R. § 1.8.
- ☐ The enclosed document is being transmitted via facsimile.

The fee has been calculated as shown below:

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TOTAL	14	-	20	=	0	\$18	\$0.00
INDEPENDENT	1	-	3	=	0	\$80	\$0.00
<input type="checkbox"/> FIRST PRESENTATION OF A MULTIPLE DEPENDENT CLAIM						\$270	\$0.00
						TOTAL	\$0.00

- ☐ Petition for () month(s) extension of time pursuant to 37 C.F.R. §§ 1.17 and 1.136(a). \$0.00 for the extension of time.
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Respectfully submitted,

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3672-0110P

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ATTACHMENT

(Rev. 01/22/01)



PATENT
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RESPONSE

Assistant Commissioner for Patents
Washington, DC 20231

September 7, 2001

Sir:

The following Remarks are respectfully submitted in response to the Office Action of July 6, 2001, in connection with the above-identified application.

IN THE SPECIFICATION

Please replace the paragraph beginning at page 8, line 8 with the following amended paragraph.

B
--Fig. 3b shows the current/voltage characteristic expressed respectively through the forward current in the conducting direction and backward current in the blocking direction of a diode according to prior art (solid lines) and of a diode made according to the method of the present invention (lines with circles/dots). The known diode is made with P3HT as the semiconducting material, spin-coated at 600 rpm from a 5 mg/ml solution and arranged between a copper anode and an aluminium cathode, respectively. The current in the forward direction is